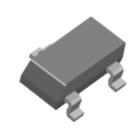
Analog Power AM2326N

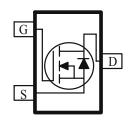
## N-Channel 20-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize High Cell Density process. Low  $r_{DS(on)}$  assures minimal power loss and conserves energy, making this device ideal for use in power management circuitry. Typical applications are DC-DC converters, power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

- Low r<sub>DS(on)</sub> Provides Higher Efficiency and Extends Battery Life
- Miniature SOT-23 Surface Mount Package Saves Board Space

PRODUCT SUMMARY 🔊				
V <sub>DS</sub> (V)	r <sub>DS(on)</sub> (Q	<b>I</b> <sub>D</sub> (A)		
	$0.070 @ V_{GS} = 4.5V$	2.2		
20	$0.080$ $V_{GS} = 2.5$ $V_{GS} = 2.5$	2.0		
	$0.128 @ V_{GS} = 1.8V$	1.8		





ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	Maximum	Units	
Drain-Source Voltage			20	V	
Gate-Source Voltage			±8	v	
	$T_A=25^{\circ}C$	] ] T_	2.2		
Continuous Drain Current <sup>a</sup>	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	1D	1.8	A	
Pulsed Drain Current <sup>b</sup>			8		
Continuous Source Current (Diode Conduction) <sup>a</sup>		$I_S$	0.6	A	
D a	$T_A=25^{\circ}C$	D	1.25	W	
Power Dissipation <sup>a</sup>	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	LD	0.8		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
M · I · · · a	t <= 5 sec	$R_{\mathrm{THJA}}$	100	°C/W	
Maximum Junction-to-Ambient <sup>a</sup>	Steady-State	КТНЈА	166	C/W	

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## Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Parameter	Symbol	Took Conditions	Limits			T 124	
Farameter	Symbol	<b>Test Conditions</b>	Min	Тур	Max	Unit	
Static							
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \text{ uA}$	0.70				
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}, V_{GS} = 12 \text{ V}$			1	uA	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}$			0.1	uA	
Zero Gate Voltage Drain Current	<sup>1</sup> DSS	$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			1		
On-State Drain Current <sup>A</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	5			A	
		$V_{GS} = 4.5 \text{ V}, I_D = 2.2 \text{ A}$			70		
Drain-Source On-Resistance <sup>A</sup>	r <sub>DS(on)</sub>	$V_{GS} = 2.5 \text{ V}, I_D = 2.0 \text{ A}$			80	mΩ	
		$V_{GS} = 1.8 \text{ V}, I_D = 1.8 \text{ A}$			120		
Forward Tranconductance <sup>A</sup>	$g_{\mathrm{fs}}$	$V_{DS} = 5 \text{ V}, I_{D} = 2.0 \text{ A}$		11		S	
Diode Forward Voltage	$V_{\mathrm{SD}}$	$I_S = 0.6 \text{ A}, V_{GS} = 0 \text{ V}$		0.60		V	
Dynamic <sup>b</sup>							
Total Gate Charge	$Q_{g}$	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V},$		4.5		nC	
Gate-Source Charge	$Q_{gs}$	$I_{DS} = 2.0 \text{ A}$		0.89			
Gate-Drain Charge	$Q_{gd}$	ID - 2.0 A		0.95			
Turn-On Delay Time	$t_{d(on)}$			6			
Rise Time	$t_{\rm r}$	$V_{DD}$ = 10 V, Id = 1.0 A , $R_G$ = 6 $\Omega,$		6.5		ne	
Turn-Off Delay Time	$t_{d(off)}$	$V_{Gs} = 4.5 \text{ V}$		14		ns	
Fall-Time	$t_{\mathrm{f}}$			2			

## Notes

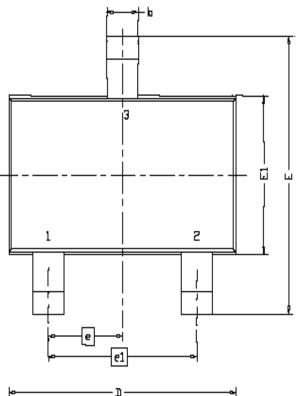
- a. Pulse test:  $PW \le 300$ us duty cycle  $\le 2\%$ .
- b. Guaranteed by design, not subject to production testing.

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## Package Information

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DIM,	MILLIMETERS			
	MIN	NDM	MAX	
Α	0.935	0.95	1.10	
A1	0.01	-	0.10	
A2	0.85	0.90	0.925	
Ь	0.30	0.40	0.50	
С	0.10	0.15	0,25	
D	2.70	2.90	3.10	
П	2.60	2.80	3.00	
E1	1.40	1.60	1.80	
6	0.95 BSC			
el	1.90 BSC			
L	0.30	0.40	0.60	
L1	0.60REF			
LZ	0.25BSC			
R	0.10			
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01	7*N□M			

